2-Input NOR Gate / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHC1GT02 is a single gate 2–input NOR fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0V CMOS logic to 5.0V CMOS Logic or from 1.8V CMOS logic to 3.0V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT02 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1GT02 to be used to interface 5V circuits to 3V circuits. The output structures also provide protection when $V_{CC} = 0V$. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 4.7$ ns (Typ) at $V_{CC} = 5V$
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL–Compatible Inputs: $V_{IL} = 0.8V$; $V_{IH} = 2.0V$
- CMOS–Compatible Outputs: $V_{OH} > 0.8V_{CC}$; $V_{OL} < 0.1V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V

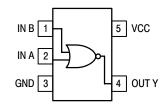


Figure 1. 5-Lead SOT-353 Pinout (Top View)

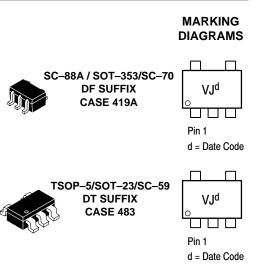


Figure 2. Logic Symbol



ON Semiconductor

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PIN ASSIGNMENT					
1	IN B				
2	IN A				
3	GND				
4	OUT Y				
5	VCC				

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	V _{IN}	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	I _{OK}	+20	mA
DC Output Current, per Pin	I _{OUT}	+25	mA
DC Supply Current, V _{CC} and GND	I _{CC}	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC-88A Package: -5 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V _{CC}	3.0	5.5	V
DC Input Voltage	V _{IN}	0.0	5.5	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	0.0 0.0	5.5 V _{CC}	V
Operating Temperature Range	T _A	-55	+125	°C
Input Rise and Fall Time $\begin{array}{ll} V_{CC}=3.3V\pm0.3V\\ V_{CC}=5.0V\pm0.5V \end{array}$	t _r , t _f	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

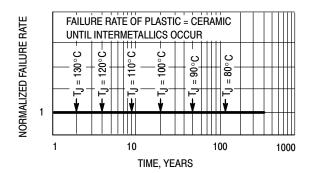


Figure 3. Failure Rate vs. Time Junction Temperature

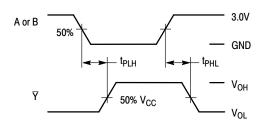
			V _{CC}	ר	Γ _A = 25°0	C	T _A ≤	85°C	TA ≤ <i>'</i>	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Мах	Min	Мах	Min	Max	Unit
V _{IH}	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
$V_{IN} = V_{IH} \text{ or } V_{IL}$		3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V	
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA
I _{CCT}	Quiescent Supply Current	Per Input: $V_{IN} = 3.4V$ Other Input: V_{CC} or GND	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0.0			0.5		5.0		10	μA

DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_r = t_f = 3.0 \text{ns}$)

				٦	Γ _A = 25°0	2	TA ≤	85°C	TA ≤ <i>'</i>	125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propogation Delay,	$V_{CC} = 3.0 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		4.5 5.8	10.0 13.5		11.0 15.0		13.0 17.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15 pF C _L = 50 pF		3.0 3.8	6.7 7.7		7.5 8.5		8.5 9.5	
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF
						Ту	pical @	25°C, V	_{CC} = 5.0	v	
C _{PD}	Power Dissipation Capa	acitance (Note 1.)						11			pF

 C_PD 1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



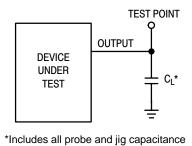
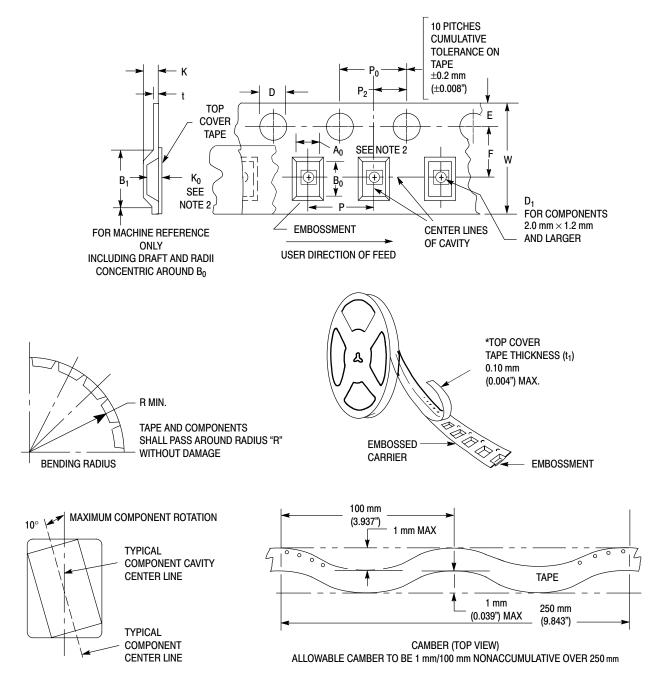


Figure 4. Switching Waveforms

Figure 5. Test Circuit

DEVICE ORDERING	INFORMA	TION						
			Device Nome	enclature				
Device Order Number	Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape and Reel Size
MC74VHC1GT02DFT2	MC	74	VHC1G	T02	DF	T2	SC-88A / SOT-353 / SC-70	178 mm (7") 3000 Unit
MC74VHC1GT02DFT4	MC	74	VHC1G	T02	DF	T4	SC-88A / SOT-353 / SC-70	330 mm (13") 10000 Unit
MC74VHC1GT02DTT1	MC	74	VHC1G	T02	DT	T1	TSOPS / SOT-23 / SC-59	178 mm (7") 3000 Unit
MC74VHC1GT02DTT3	MC	74	VHC1G	T02	DT	Т3	TSOPS / SOT-23 / SC-59	330 mm (13") 10000 Unit





Tape Size	B ₁ Max	D	D ₁	E	F	к	Р	P ₀	P ₂	R	т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED	CARRIER	DIMENSIONS	(See	Notes	1	and 2)
LINDOOOLD	OANNEN	DIMILINGIONO	(000	110163		anu z

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

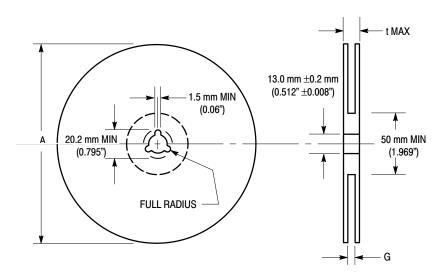
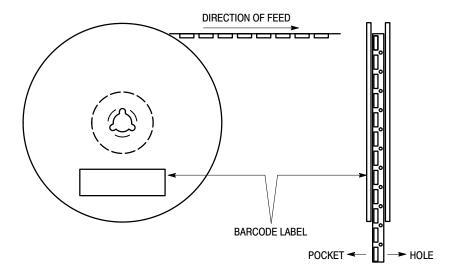


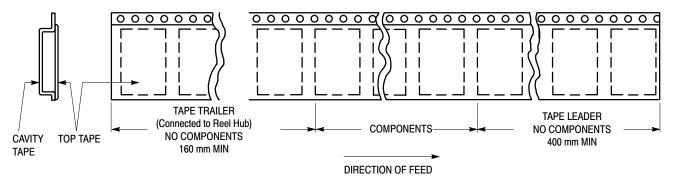
Figure 7. Reel Dimensions

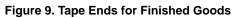
REEL DIMENSIONS

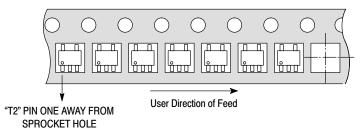
Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, −0.0 (0.33" + 0.059", −0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")

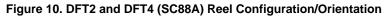












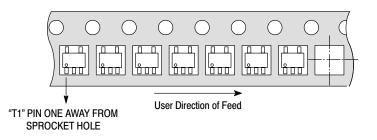
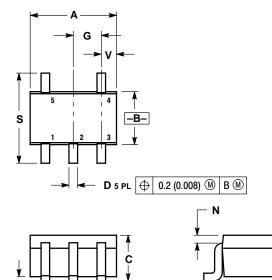


Figure 11. DTT1 and DTT3 (TSOP5) Reel ConfigurationOrientation

SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 ISSUE B

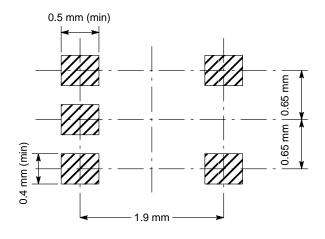


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NOT	ES:
1.	DIMENSIONING AND TOLERANCING PER ANSI
	Y14.5M, 1982.
2.	CONTROLLING DIMENSION: MM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
Н		0.004		0.10
ſ	0.004	0.010	0.10	0.25
Κ	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
٧	0.012	0.016	0.30	0.40



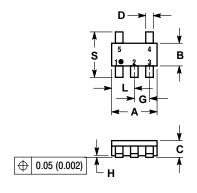
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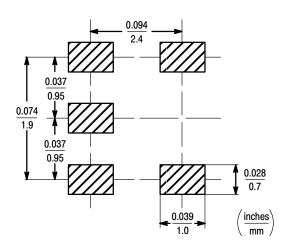
TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE CASE 483-01 **ISSUE A**

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NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
Κ	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0°	10 °
S	2.50	3.00	0.0985	0.1181





<u>Notes</u>

<u>Notes</u>

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